FKS0048A

N-Ch 100V Fast Switching MOSFETs

Features

- Advanced Trench MOS Technology
- Fast Switching Speed
- 100% EAS Guaranteed
- Green Device Available

Product Summary

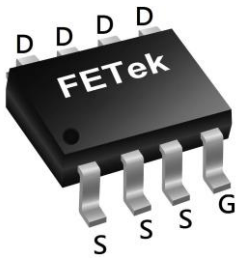
Green

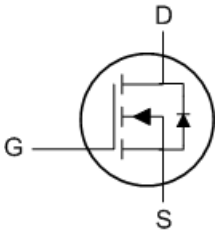
BVDSS	RDSON	ID
100V	8mΩ	13.5A

Applications

- High Frequency Switching and Synchronous Rectification.
- DC/DC Converter.

SOP8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current[1]	13.5	A
I_D@T_A=70°C	Continuous Drain Current[1]	10.5	A
I_{DM}	Pulsed Drain Current[2]	55	A
EAS	Single Pulse Avalanche Energy[3]	49	mJ
I_{AS}	Avalanche Current	14	A
P_D@T_C=25°C	Total Power Dissipation[4]	3.1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient[1] (t≦10S)	---	40	°C/W
	Thermal Resistance Junction-ambient[1] (Steady State)	---	75	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case[1]	---	24	°C/W

Electrical Characteristics (T_J=25 ˚C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=13.5A	---	6.6	8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25˚C	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55˚C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=13.5A	---	75	---	S
Qg	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=13.5A	---	45	---	nC
Qgs	Gate-Source Charge		---	9.5	---	
Qgd	Gate-Drain Charge		---	4.8	---	
Td(on)	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3Ω, I_D=13.5A	---	10	---	ns
Tr	Rise Time		---	6.5	---	
Td(off)	Turn-Off Delay Time		---	45	---	
Tf	Fall Time		---	7.5	---	
Ciss	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	3148	---	pF
Coss	Output Capacitance		---	693	---	
Crss	Reverse Transfer Capacitance		---	26	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5,6]	V_G=V_D=0V , Force Current	---	---	13.5	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25˚C	---	---	1.1	V
t_{rr}	Reverse Recovery Time	I_F=13.5A , di/dt=100A/μs , T_J=25˚C	---	33	---	nS
Q_{rr}	Reverse Recovery Charge		---	150	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.5mH,I_{AS}=14A
4.The power dissipation is limited by 175˚C junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

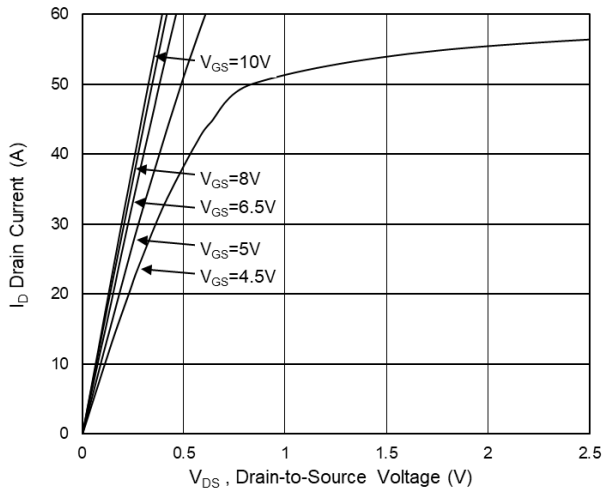


Fig.1 Typical Output Characteristics

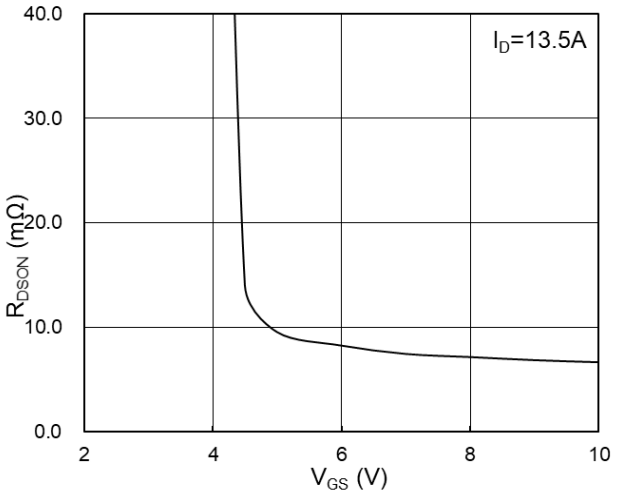


Fig.2 On-Resistance vs G-S Voltage

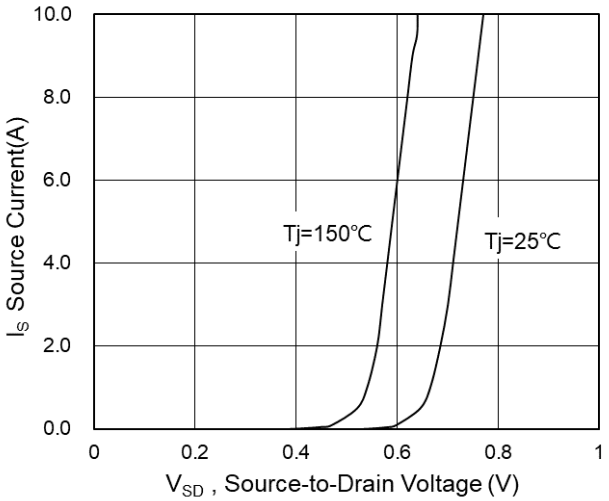


Fig.3 Source Drain Forward Characteristics

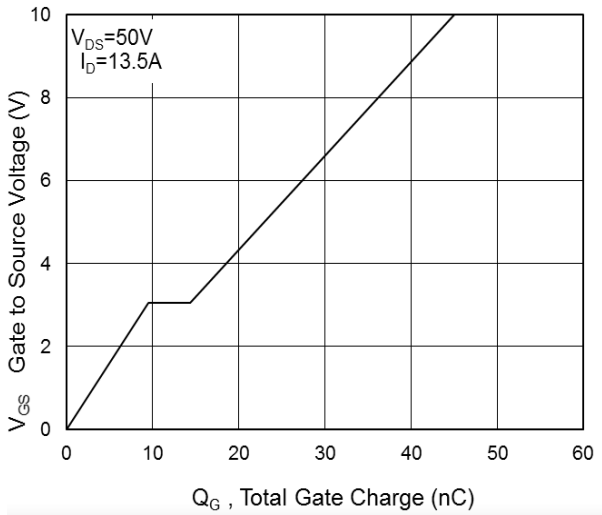


Fig.4 Gate-Charge Characteristics

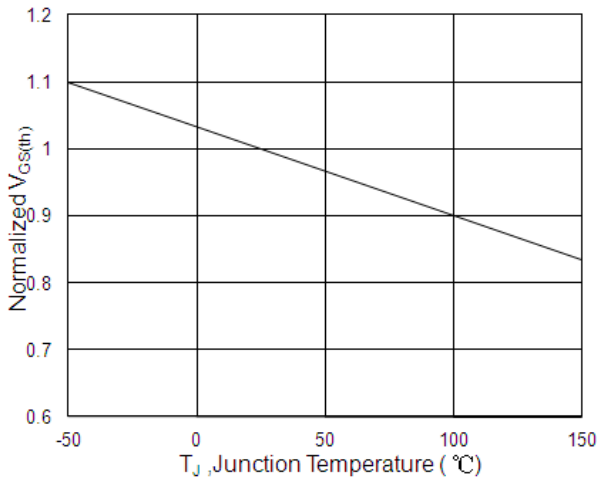


Fig.5 Normalized $V_{GS(th)}$ vs T_J

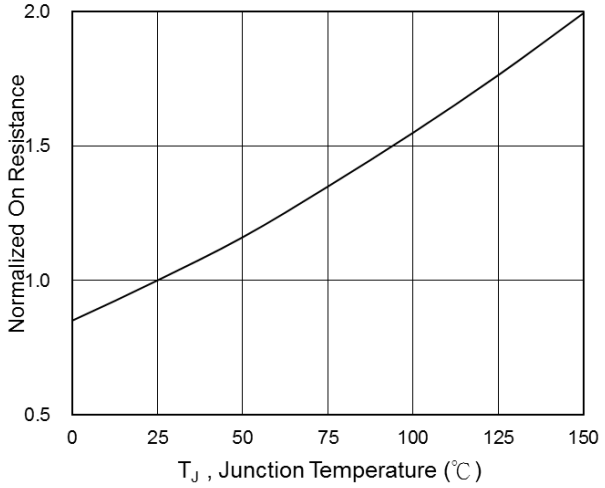


Fig.6 Normalized R_{DSON} vs T_J

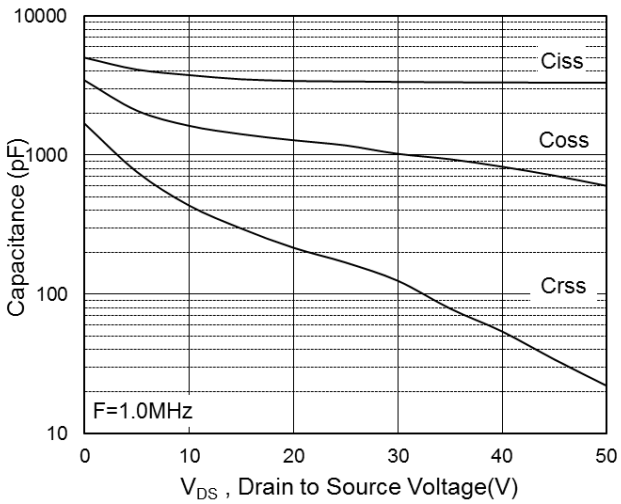


Fig.7 Capacitance

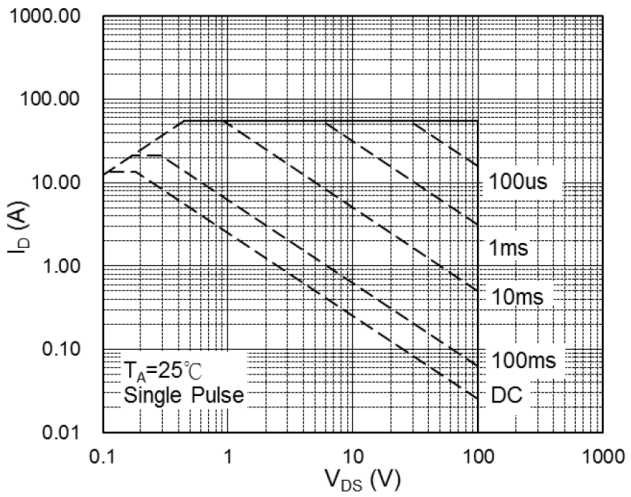


Fig.8 Safe Operating Area

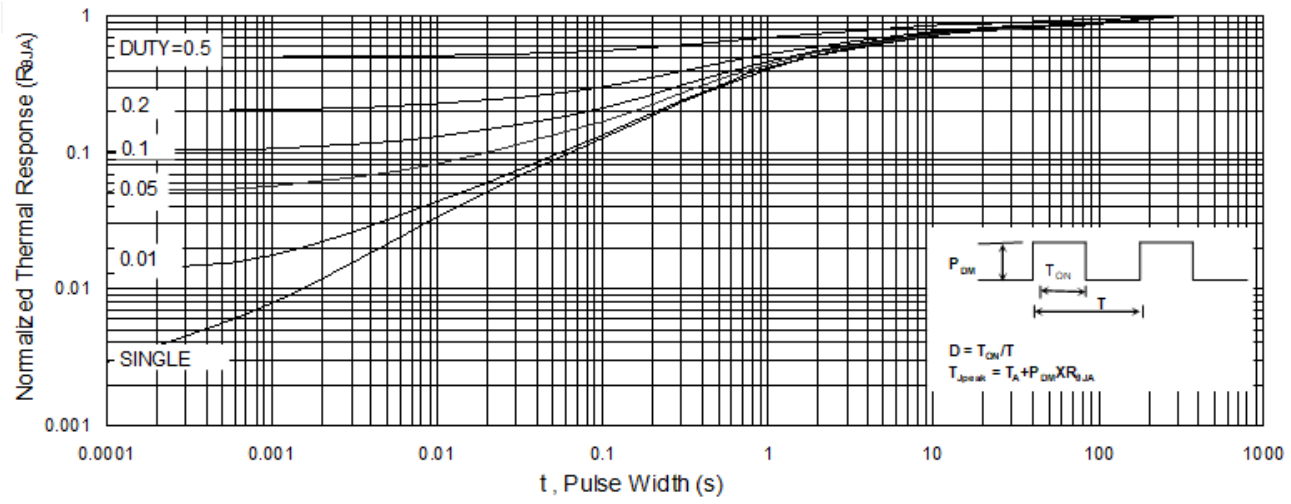


Fig.9 Normalized Maximum Transient Thermal Impedance

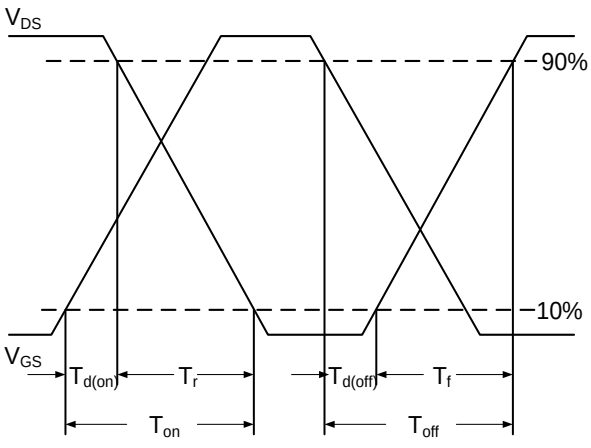


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

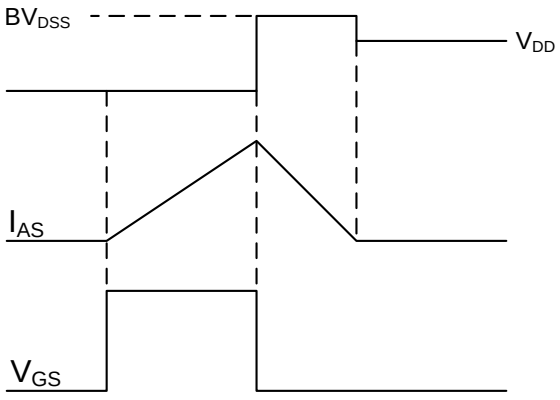


Fig.11 Unclamped Inductive Waveform